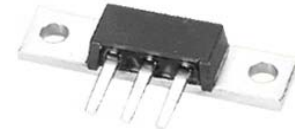


# Silicon Power Schottky Diode

 $V_{RRM} = 20\text{ V} - 100\text{ V}$ 
 $I_F = 80\text{ A}$ 

## Features

- High Surge Capability
- Types up to 100V  $V_{RRM}$

**D61-3M Package**


## Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	FST8320M	FST78330M	FST8335M	FST8340M	Unit
Repetitive peak reverse voltage	$V_{RRM}$		20	30	35	40	V
RMS reverse voltage	$V_{RMS}$		14	21	35	28	V
DC blocking voltage	$V_{DC}$		20	30	35	40	V
Continuous forward current	$I_F$	$T_C \leq 110\text{ °C}$	80	80	80	80	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	800	800	800	800	A
Operating temperature	$T_j$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C
Storage temperature	$T_{stg}$		-40 to 175	-40 to 175	-40 to 175	-40 to 175	°C

## Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	FST8320M	FST8330M	FST8335M	FST78340M	Unit
Diode forward voltage	$V_F$	$I_F = 80\text{ A}$ , $T_j = 25\text{ °C}$	0.65	0.65	0.65	0.65	V
Reverse current	$I_R$	$V_R = 20\text{ V}$ , $T_j = 25\text{ °C}$	1.5	1.5	1.5	1.5	mA
		$V_R = 20\text{ V}$ , $T_j = 125\text{ °C}$	500	500	500	500	

## Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		1.2	1.2	1.2	1.2	°C/W
-------------------------------------	------------	--	-----	-----	-----	-----	------

Figure .1-Typical Forward Charac teristics

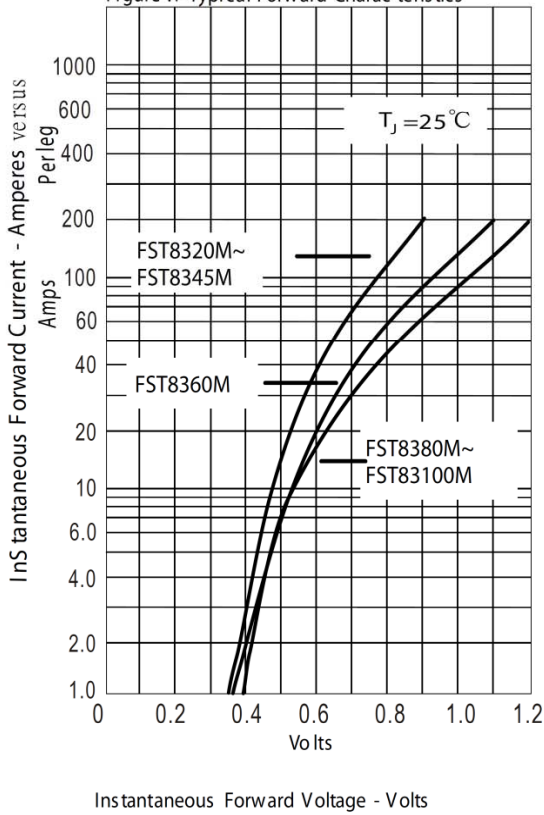


Figure .2- Forward Derating Curve

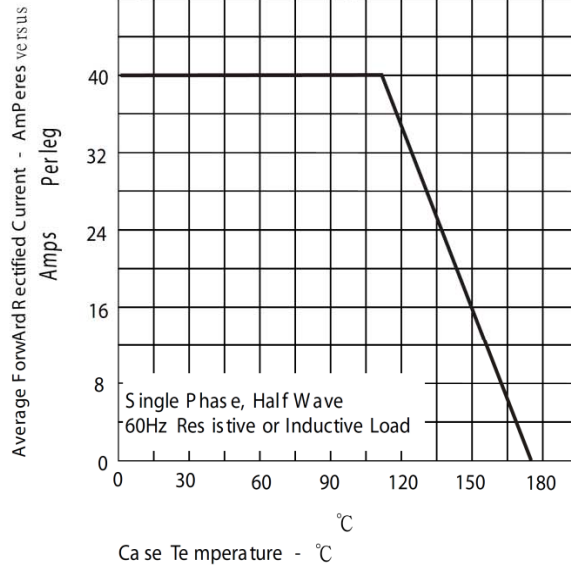


Figure .4-Typical Reverse Charac teristics

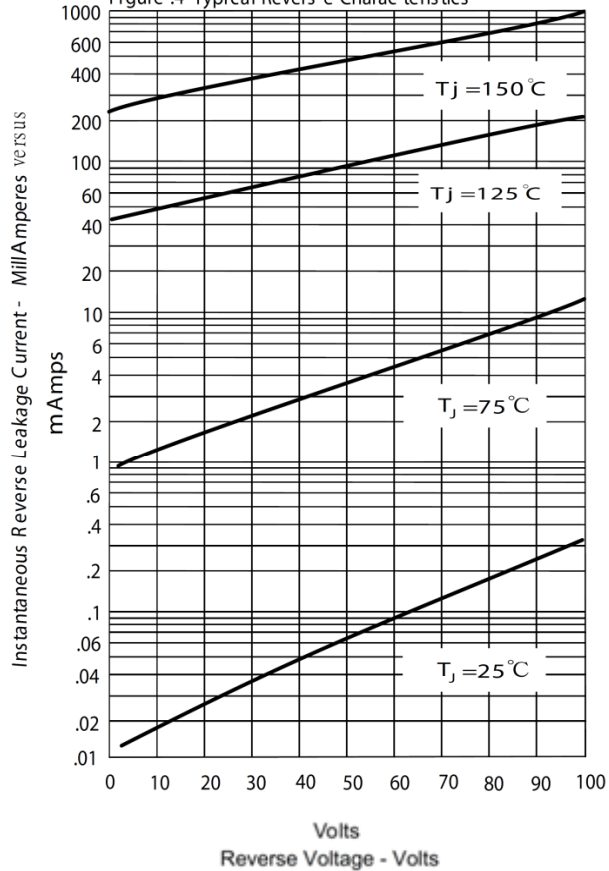


Figure .3-Peak Forward Surge Current

